Correction to: Investigations of the photoelectrochemical properties of different contents In of $\text{In}_x\text{Ga}_{1-x}\text{N}$ in CO_2 reduction

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Published online: 12 October 2021
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Correction to: Research on Chemical Intermediates

<https://doi.org/10.1007/s11164-021-04556-x>

In Fig. 5b, The $\text{In}_{0.009}\text{GaN}_{0.0991}/\text{GaN}$ should be changed to $\text{In}_{0.071}\text{GaN}_{0.0929}/\text{GaN}$. The author apologizes for this error.

The original article can be found online at <https://doi.org/10.1007/s11164-021-04556-x>.

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Fig. 5 XRD of $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ ($x=0.009$ and 0.071) electrodes before and after CO_2 conversion. **a** $\text{In}_{0.009}\text{Ga}_{0.991}\text{N}/\text{GaN}$; **b** $\text{In}_{0.071}\text{Ga}_{0.929}\text{N}/\text{GaN}$

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